

WHAT IS CLAIMED IS:

1. A thin film transistor comprising:
 - a source, a drain, and a channel located between said source and said drain;
 - 5 a gate electrode provided adjacent to said channel with a gate insulating layer therebetween;
 - a lightly doped region provided between said channel and at least one of said source and said drain; and
 - 10 a silicon nitride region provided in contact with said lightly doped region.